



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Patent Application of

Shunpei YAMAZAKI et al.

Serial No. 09/118,010

Filed: July 17, 1998

For: SEMICONDUCTOR DEVICE,
METHOD OF FABRICATING SAME,
AND ELECTROOPTICAL DEVICE

) Art Unit: 2822

) Examiner: M. Guerrero

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on March 17, 2003.

Adele M. Stamper
Adele M. Stamper

AMENDMENT AFTER FINAL

Honorable Commissioner of Patents
Washington, D.C. 20231

RECEIVED

MAR 26 2003

OFFICE OF PETITIONS

Sir:

In response to the Office Action dated November 22, 2002 please amend the above-identified application as follows:

IN THE CLAIMS:

31

47. (Amended) A semiconductor device comprising:

a first resinous substrate having an uneven surface, and a second resinous substrate opposed to said first resinous substrate;

a resinous layer provided on said uneven surface of said first resinous substrate and having a planarized surface; and

a thin-film transistor provided on said planarized surface of said resinous layer;

an interlayer insulating layer comprising a resinous material provided over said thin-film transistor; and

at least one pixel electrode provided on said interlayer insulating layer, wherein said thin-film transistor comprises:

a semiconductor layer comprising a source region, a drain region, and a channel formation region between said source region and said drain region; and

*RECEIVED
MAY 2003
U.S. PATENT & TRADEMARK OFFICE
SEARCHED
INDEXED
MAILED*